

# MOSFET

## OptiMOS™ 6 Power-Transistor, 120 V

### Features

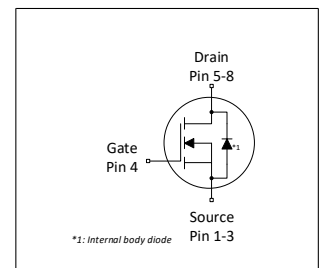
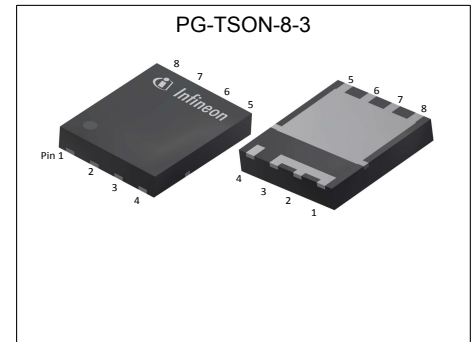
- N-channel, normal level
- Very low on-resistance  $R_{DS(on)}$
- Excellent gate charge x  $R_{DS(on)}$  product (FOM)
- Very low reverse recovery charge ( $Q_{rr}$ )
- High avalanche energy rating
- 175°C operating temperature
- Optimized for high frequency switching and synchronous rectification
- Pb-free lead plating; RoHS compliant
- Halogen-free according to IEC61249-2-21
- MSL 1 classified according to J-STD-020

### Product validation

Fully qualified according to JEDEC for Industrial Applications

**Table 1 Key Performance Parameters**

Parameter	Value	Unit
$V_{DS}$	120	V
$R_{DS(on),max}$	3.04	m $\Omega$
$I_D$	194	A
$Q_{oss}$	139	nC
$Q_G$	59	nC
$Q_{rr}$ (1000 A/ $\mu$ s)	228	nC



RoHS

Type / Ordering Code	Package	Marking	Related Links
ISC030N12NM6	PG-TSON-8	03012N6	-

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## 1 Maximum ratings

at  $T_A=25\text{ °C}$ , unless otherwise specified

**Table 2 Maximum ratings**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current <sup>1)</sup>	$I_D$	-	-	194 137 124 21	A	$V_{GS}=10\text{ V}$ , $T_C=25\text{ °C}$ $V_{GS}=10\text{ V}$ , $T_C=100\text{ °C}$ $V_{GS}=8\text{ V}$ , $T_C=100\text{ °C}$ $V_{GS}=10\text{ V}$ , $T_A=25\text{ °C}$ , $R_{THJA}=50\text{ °C/W}^{2)}$
Pulsed drain current <sup>3)</sup>	$I_{D,pulse}$	-	-	776	A	$T_A=25\text{ °C}$
Avalanche current, single pulse <sup>4)</sup>	$I_{AS}$	-	-	50	A	$T_C=25\text{ °C}$
Avalanche energy, single pulse	$E_{AS}$	-	-	1483	mJ	$I_D=18\text{ A}$ , $R_{GS}=25\text{ }\Omega$
Gate source voltage	$V_{GS}$	-20	-	20	V	-
Power dissipation	$P_{tot}$	-	-	250 3.0	W	$T_C=25\text{ °C}$ $T_A=25\text{ °C}$ , $R_{THJA}=50\text{ °C/W}^{2)}$
Operating and storage temperature	$T_j$ , $T_{stg}$	-55	-	175	°C	-

## 2 Thermal characteristics

**Table 3 Thermal characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case, bottom	$R_{thJC}$	-	-	0.6	°C/W	-
Thermal resistance, junction - case, top	$R_{thJC}$	-	-	20	°C/W	-
Thermal resistance, junction - ambient, 6 cm <sup>2</sup> cooling area <sup>2)</sup>	$R_{thJA}$	-	-	50	°C/W	-

<sup>1)</sup> Rating refers to the product only with datasheet specified absolute maximum values, maintaining case temperature as specified. For other case temperatures please refer to Diagram 2. De-rating will be required based on the actual environmental conditions.

<sup>2)</sup> Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm<sup>2</sup> (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

<sup>3)</sup> See Diagram 3 for more detailed information.

<sup>4)</sup> See Diagram 13 for more detailed information.

### 3 Electrical characteristics

at  $T_j=25\text{ °C}$ , unless otherwise specified

**Table 4 Static characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	120	-	-	V	$V_{GS}=0\text{ V}$ , $I_D=1\text{ mA}$
Gate threshold voltage	$V_{GS(th)}$	2.6	3.1	3.6	V	$V_{DS}=V_{GS}$ , $I_D=141\text{ }\mu\text{A}$
Zero gate voltage drain current	$I_{DSS}$	-	0.1 10	1 100	$\mu\text{A}$	$V_{DS}=100\text{ V}$ , $V_{GS}=0\text{ V}$ , $T_j=25\text{ °C}$ $V_{DS}=100\text{ V}$ , $V_{GS}=0\text{ V}$ , $T_j=125\text{ °C}$
Gate-source leakage current	$I_{GSS}$	-	10	100	nA	$V_{GS}=20\text{ V}$ , $V_{DS}=0\text{ V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	2.5 2.9	3.04 3.7	$\text{m}\Omega$	$V_{GS}=10\text{ V}$ , $I_D=50\text{ A}$ $V_{GS}=8\text{ V}$ , $I_D=25\text{ A}$
Gate resistance	$R_G$	0.42	0.84	1.26	$\Omega$	-
Transconductance	$g_{fs}$	55	110	-	S	$ V_{DS} \geq 2 I_D R_{DS(on)max}$ , $I_D=50\text{ A}$

**Table 5 Dynamic characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	$C_{iss}$	-	4200	5500	pF	$V_{GS}=0\text{ V}$ , $V_{DS}=60\text{ V}$ , $f=1\text{ MHz}$
Output capacitance <sup>1)</sup>	$C_{oss}$	-	1200	1600	pF	$V_{GS}=0\text{ V}$ , $V_{DS}=60\text{ V}$ , $f=1\text{ MHz}$
Reverse transfer capacitance <sup>1)</sup>	$C_{rss}$	-	23	40	pF	$V_{GS}=0\text{ V}$ , $V_{DS}=60\text{ V}$ , $f=1\text{ MHz}$
Turn-on delay time	$t_{d(on)}$	-	12	-	ns	$V_{DD}=60\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=25\text{ A}$ , $R_{G,ext}=1.6\text{ }\Omega$
Rise time	$t_r$	-	7.6	-	ns	$V_{DD}=60\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=25\text{ A}$ , $R_{G,ext}=1.6\text{ }\Omega$
Turn-off delay time	$t_{d(off)}$	-	19	-	ns	$V_{DD}=60\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=25\text{ A}$ , $R_{G,ext}=1.6\text{ }\Omega$
Fall time	$t_f$	-	8.8	-	ns	$V_{DD}=60\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=25\text{ A}$ , $R_{G,ext}=1.6\text{ }\Omega$

**Table 6 Gate charge characteristics<sup>2)</sup>**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge <sup>1)</sup>	$Q_{gs}$	-	20	26	nC	$V_{DD}=60\text{ V}$ , $I_D=25\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$
Gate charge at threshold <sup>1)</sup>	$Q_{g(th)}$	-	13	16	nC	$V_{DD}=60\text{ V}$ , $I_D=25\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$
Gate to drain charge <sup>1)</sup>	$Q_{gd}$	-	12.7	19	nC	$V_{DD}=60\text{ V}$ , $I_D=25\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$
Switching charge	$Q_{sw}$	-	20	-	nC	$V_{DD}=60\text{ V}$ , $I_D=25\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$
Gate charge total <sup>1)</sup>	$Q_g$	-	59	74	nC	$V_{DD}=60\text{ V}$ , $I_D=25\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$
Gate plateau voltage	$V_{plateau}$	-	4.9	-	V	$V_{DD}=60\text{ V}$ , $I_D=25\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$
Output charge <sup>1)</sup>	$Q_{oss}$	-	139	174	nC	$V_{DS}=60\text{ V}$ , $V_{GS}=0\text{ V}$

<sup>1)</sup> Defined by design. Not subject to production test.

<sup>2)</sup> See "Gate charge waveforms" for parameter definition

**Table 7 Reverse diode**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode continuous forward current	$I_S$	-	-	194	A	$T_C=25\text{ °C}$
Diode pulse current	$I_{S,pulse}$	-	-	776	A	$T_C=25\text{ °C}$
Diode forward voltage	$V_{SD}$	-	0.82	1.0	V	$V_{GS}=0\text{ V}, I_F=50\text{ A}, T_j=25\text{ °C}$
Reverse recovery time <sup>1)</sup>	$t_{rr}$	-	33	66	ns	$V_R=60\text{ V}, I_F=25\text{ A}, di_F/dt=300\text{ A}/\mu\text{s}$
Reverse recovery charge <sup>1)</sup>	$Q_{rr}$	-	73	146	nC	$V_R=60\text{ V}, I_F=25\text{ A}, di_F/dt=300\text{ A}/\mu\text{s}$
Reverse recovery time <sup>1)</sup>	$t_{rr}$	-	24	48	ns	$V_R=60\text{ V}, I_F=25\text{ A}, di_F/dt=1000\text{ A}/\mu\text{s}$
Reverse recovery charge <sup>1)</sup>	$Q_{rr}$	-	228	456	nC	$V_R=60\text{ V}, I_F=25\text{ A}, di_F/dt=1000\text{ A}/\mu\text{s}$

<sup>1)</sup> Defined by design. Not subject to production test.

### 4 Electrical characteristics diagrams

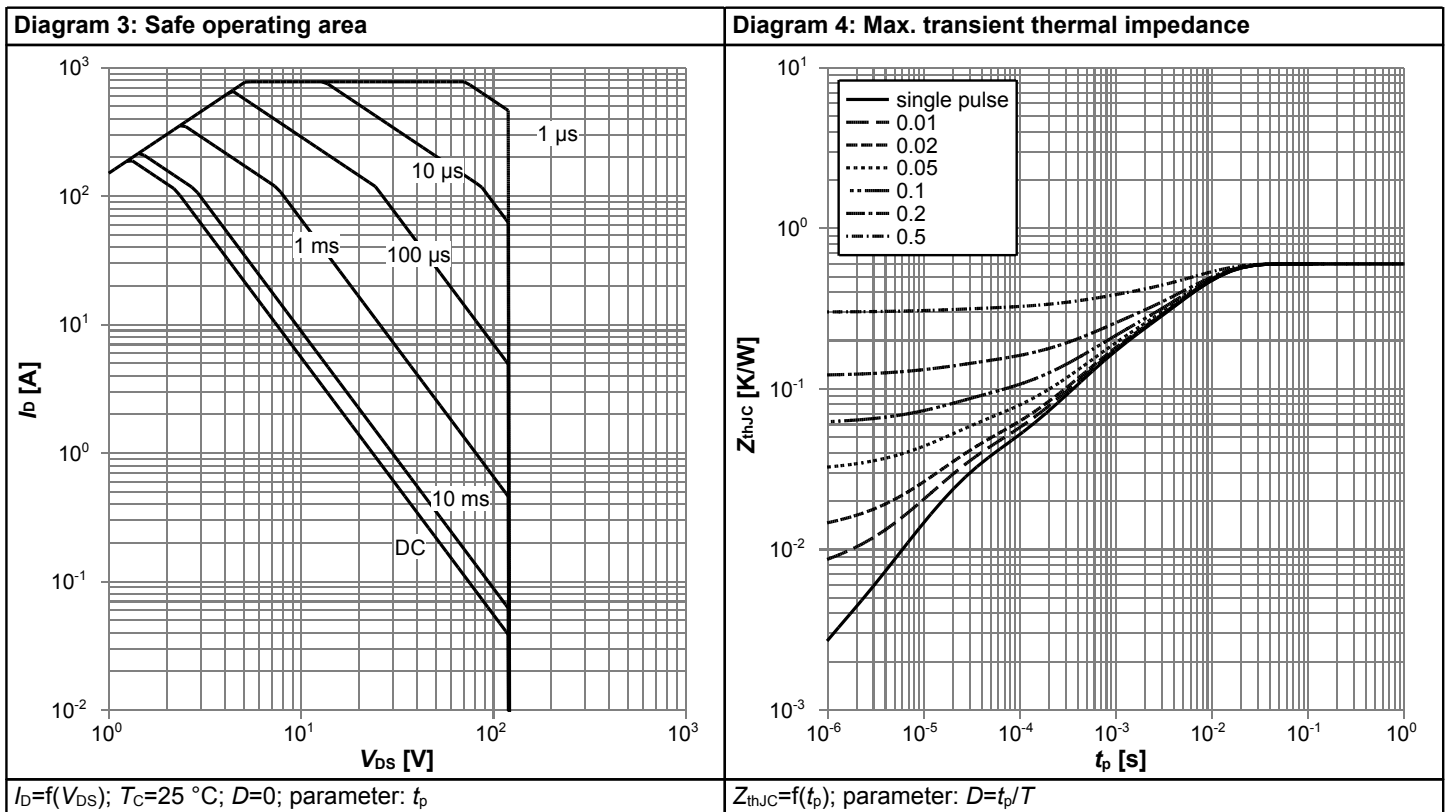
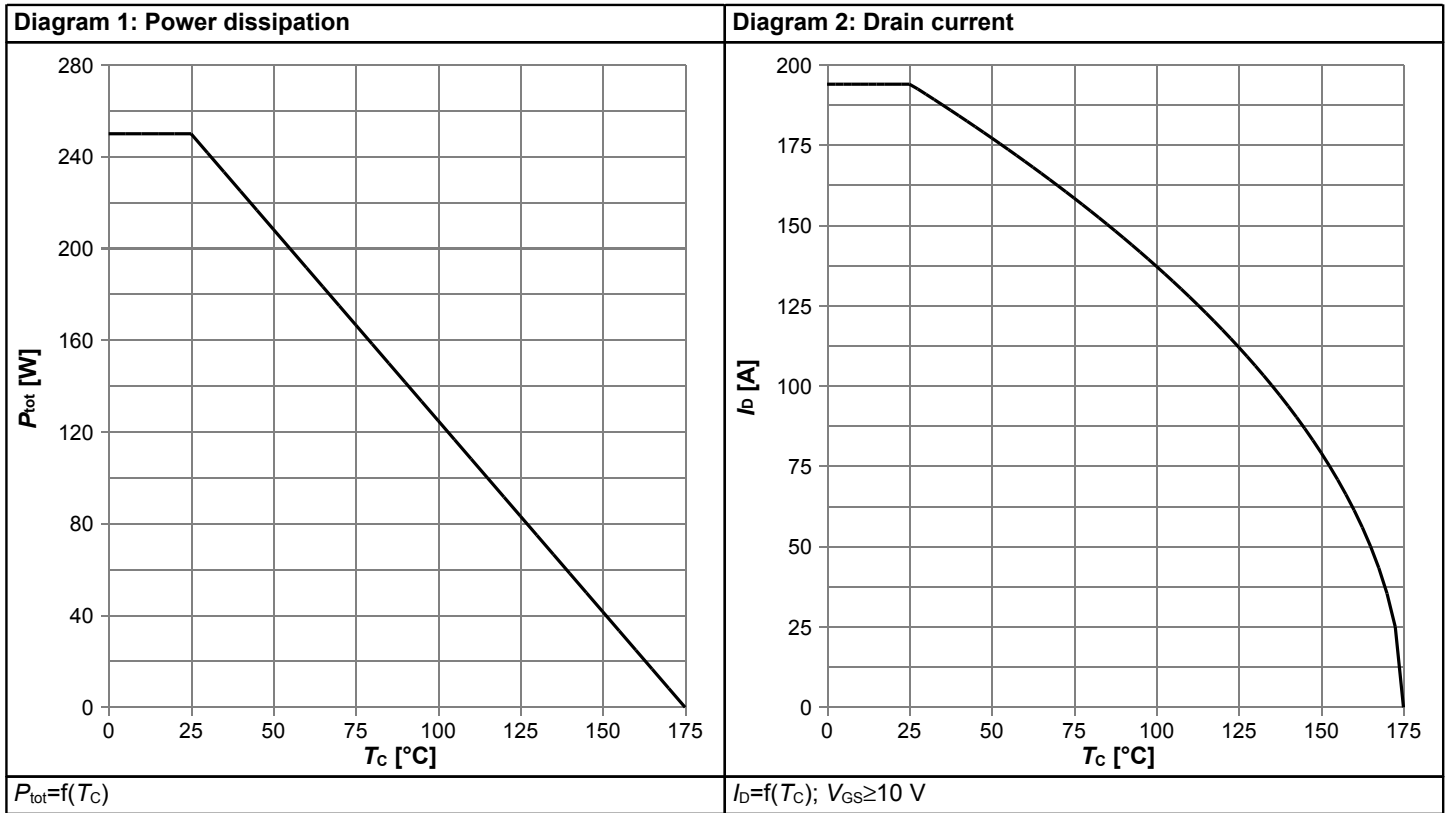
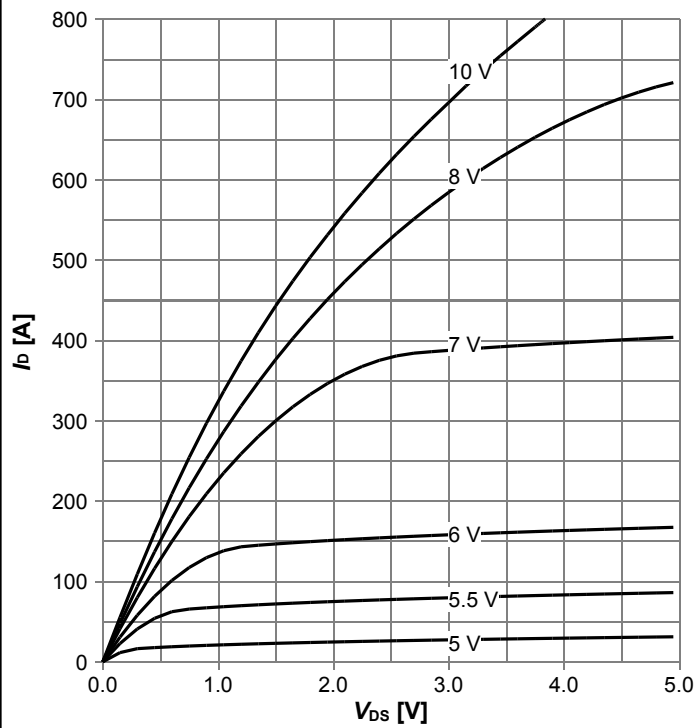
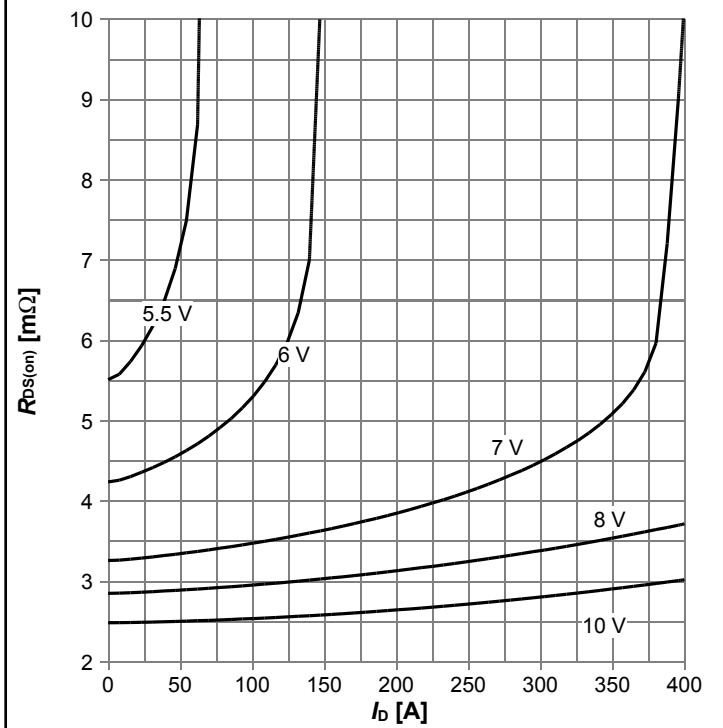


Diagram 5: Typ. output characteristics



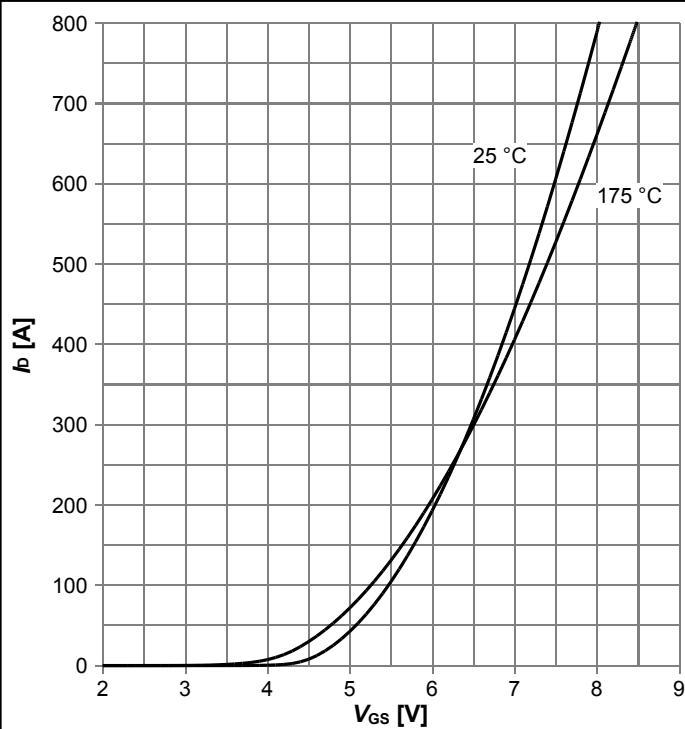
$I_D = f(V_{DS}), T_j = 25\text{ °C};$  parameter:  $V_{GS}$

Diagram 6: Typ. drain-source on resistance



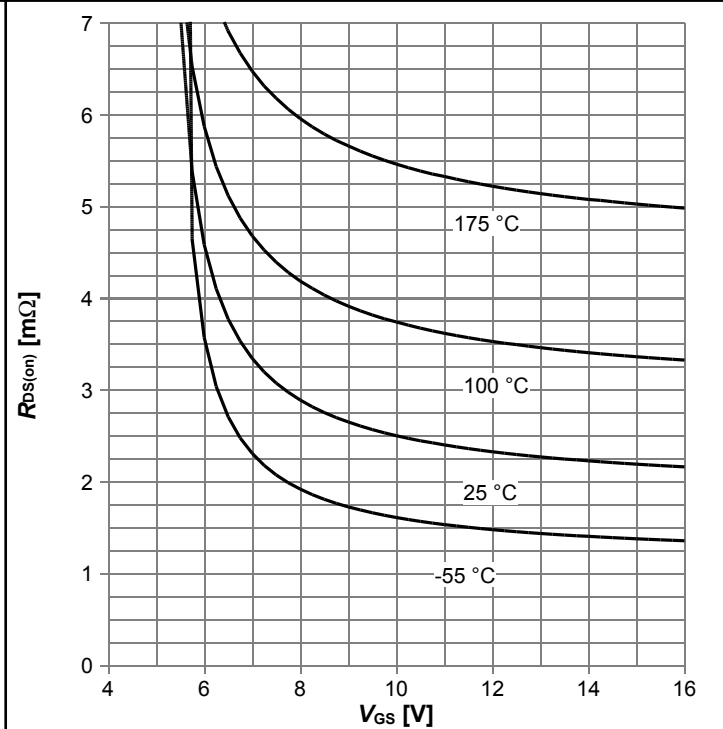
$R_{DS(on)} = f(I_D), T_j = 25\text{ °C};$  parameter:  $V_{GS}$

Diagram 7: Typ. transfer characteristics



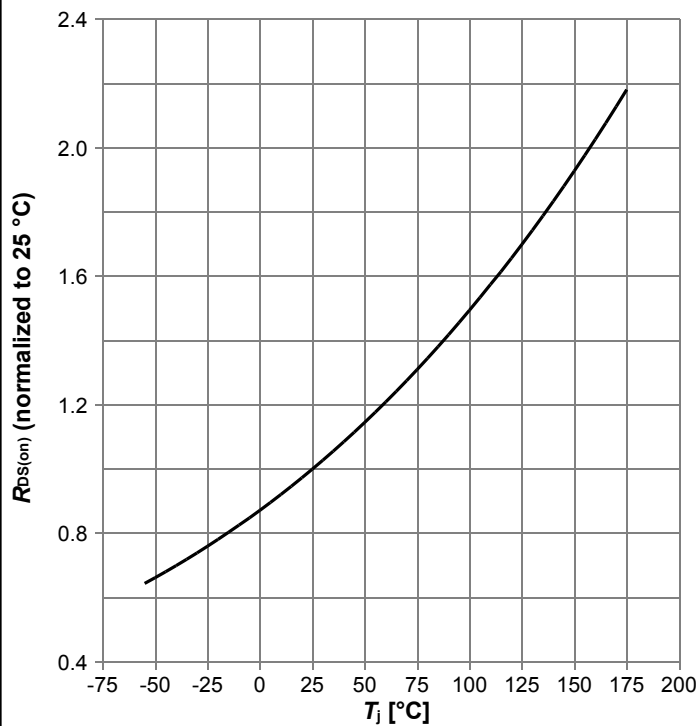
$I_D = f(V_{GS}), |V_{DS}| > 2|I_D|R_{DS(on)max};$  parameter:  $T_j$

Diagram 8: Typ. drain-source on resistance



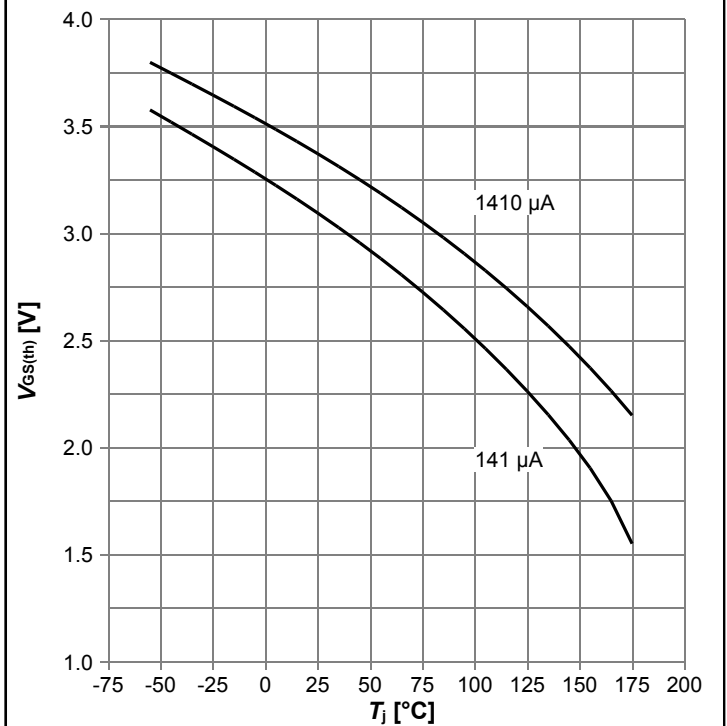
$R_{DS(on)} = f(V_{GS}), I_D = 50\text{ A};$  parameter:  $T_j$

Diagram 9: Normalized drain-source on resistance



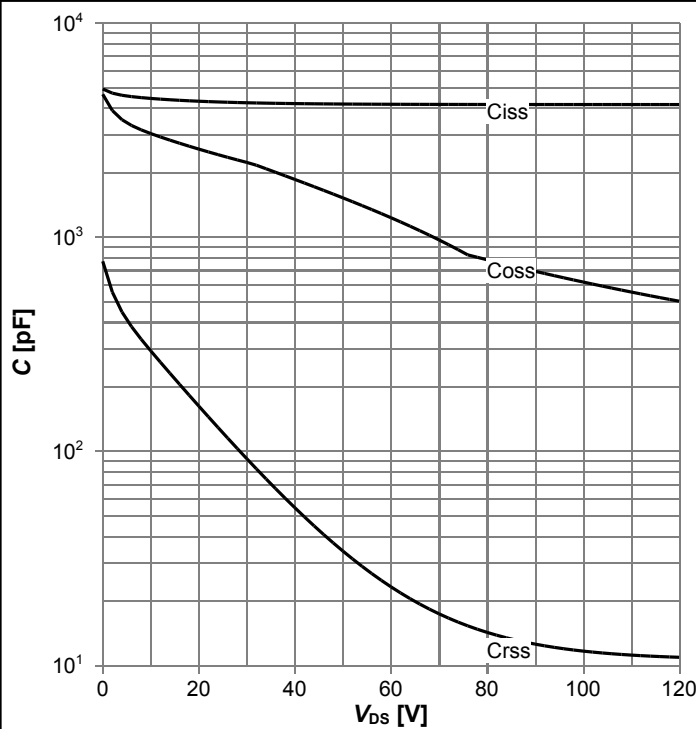
$R_{DS(on)}=f(T_j)$ ,  $I_D=50$  A,  $V_{GS}=10$  V

Diagram 10: Typ. gate threshold voltage



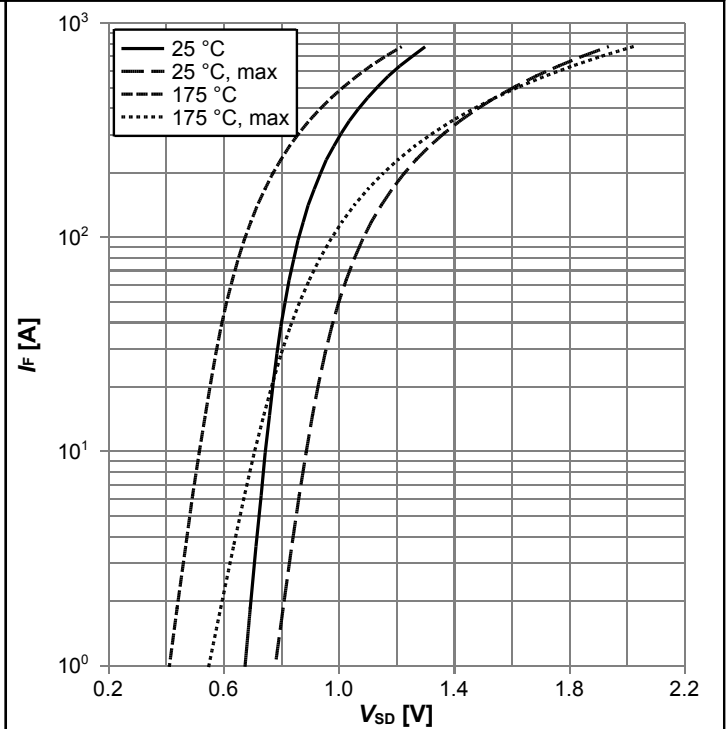
$V_{GS(th)}=f(T_j)$ ,  $V_{GS}=V_{DS}$ ; parameter:  $I_D$

Diagram 11: Typ. capacitances



$C=f(V_{DS})$ ;  $V_{GS}=0$  V;  $f=1$  MHz

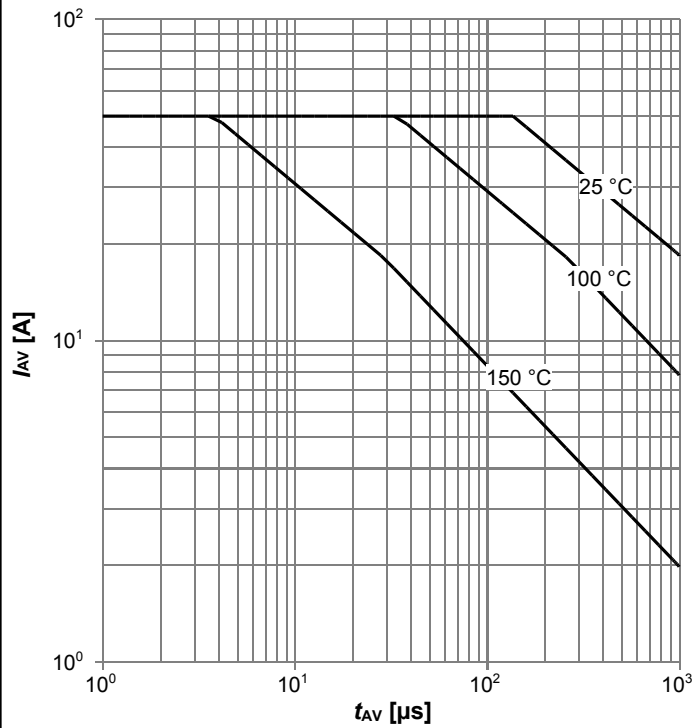
Diagram 12: Forward characteristics of reverse diode



$I_F=f(V_{SD})$ ; parameter:  $T_j$

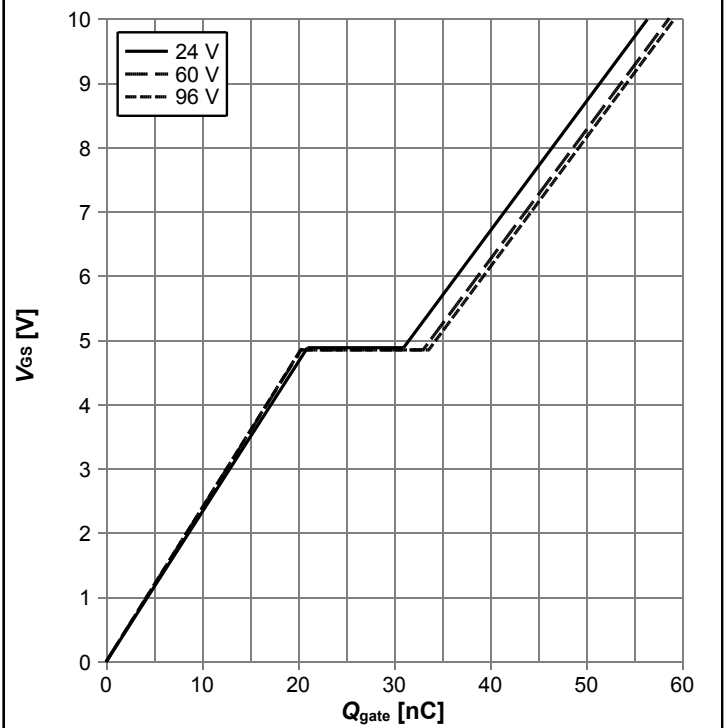


Diagram 13: Avalanche characteristics



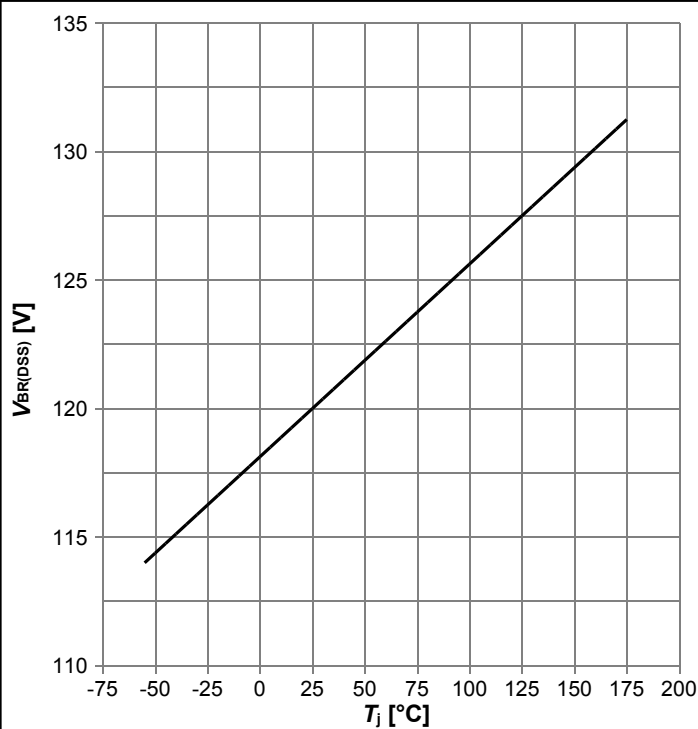
$I_{AS}=f(t_{AV}); R_{GS}=25 \Omega$ ; parameter:  $T_{j,start}$

Diagram 14: Typ. gate charge



$V_{GS}=f(Q_{gate}), I_D=25$  A pulsed,  $T_j=25$  °C; parameter:  $V_{DD}$

Diagram 15: Min. drain-source breakdown voltage

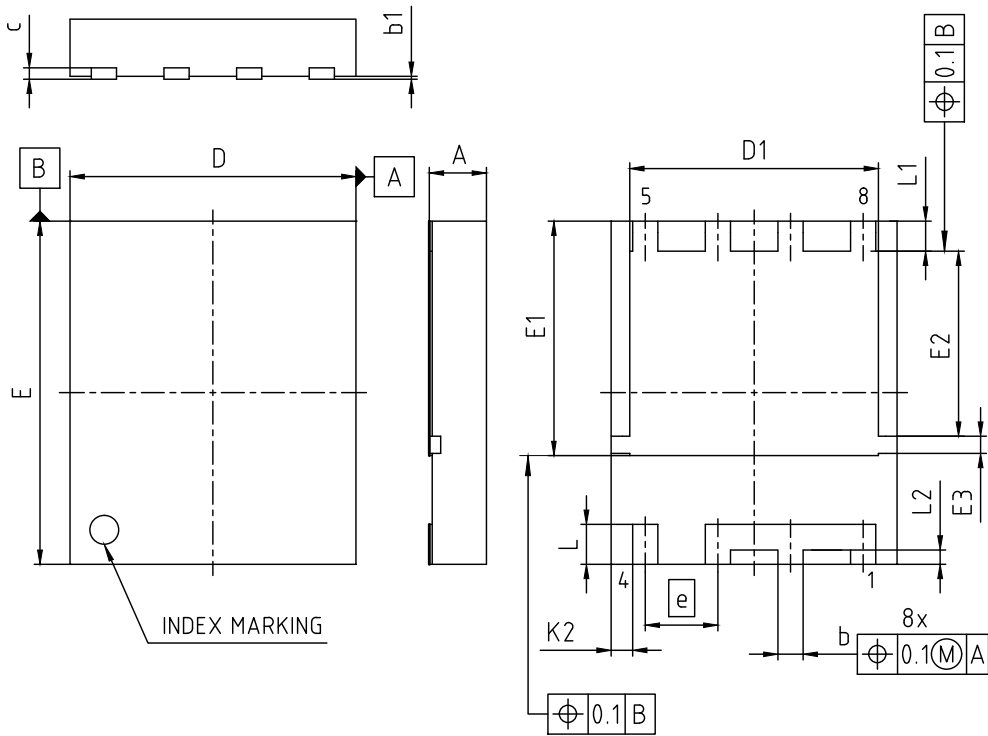


$V_{BR(DSS)}=f(T_j); I_D=1$  mA

Diagram Gate charge waveforms



### 5 Package Outlines



DIMENSION	MILLIMETERS	
	MIN.	MAX.
A	-	1.10
b	0.34	0.54
b1	-	0.05
c	0.20	
D	4.90	5.10
D1	4.25	4.45
E	5.90	6.10
E1	4.00	4.20
E2	3.14	3.34
E3	0.20	0.40
e	1.27	
K2	(0.37)	
L	0.60	0.80
L1	0.43	0.63
L2	(0.25)	

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Figure 1 Outline PG-TSON-8, dimensions in mm/inches

## Revision History

ISC030N12NM6

**Revision: 2022-12-02, Rev. 2.0**

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2022-12-02	Release of final version

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